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Ims	5,959,307	09/1999	NAKAMURA et al.	257	14 1		
¿ms	5,294,833	03/1994	SCHETZINA	857	741		
ims	5,670,798	09/1997	SCHETZINA	257	96		
							
			-N-131		<u> </u>		
							
							
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			U.S. PATENT DOCUMENTS				
*EXAMINER				22.455	CURCLASS	FILING	DATE
INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	IF APPRO	PRIATE
180951	5,793,054	08/1998	NIDO	257	118		<u> </u>
		FUF	REIGN PATENT DOCUMENTS			TRANSI	LATION
•	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO
KMI	JP 6-164085	06/1994	JAPAN			ABSTRACT	
Thus	JP 6-268259	09/1994	JAPAN			ABSTRACT	
im3	JP 6-268257	09/1994	JAPAN			ABSTRACT	
RM,	JP 7-249795	09/1995	JAPAN	//		ABSTRACT	
(m)	JP 8-070139	03/1996	JAPAN	\		ABSTRACT	
THE THE	JP 9-191160	07/1997	JAPAN			ABSTRACT	
MS	JP 7-235729	09/1995	JAPAN	7		AUSTRACT	
Sun,	JP 9-148247	06/1997	JAPAN			ABSTRACT	
ims	JP 9-148678	06/1997	JAPAN			ABSTRACT	
me	JP 6-164055	06/1994	JAPAN		1.1	ABSTRACT	
iws	JP 9-116225	05/1997	JAPAN			ABSTRACT	
ins	JP 8-064910	03/1996	JAPAN			ABSTRACT	
ims	JP 8-116128	05/1996	JAPAN		11	ABSTRACT	
ines	JP 9-129925	05/1997	JAPAN		11	ABSTRACT	
ima	JP 8-316581	11/1996	JAPAN		11	ABSTRACT	
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<u></u>	OTHER DOC	IMENTS (in	cluding Author, Title, Date, Perl	inent nages et	rc)		
	IAVASAVI et al "Stim	ulated Emissi	on by Current Injection from an AIG	N/GaN/GaInN C	Juantum Wel	Device '	'Inn I
ima	Appl. Phys., Vol. 34 (19			arv Garv Garini Q	dunitum wei		• p • .
/// 	NAKAMURA et al "H	ligh-nower In	GaN Single-Quantum-Well-Structure	Blue and Violet	Light-Emitti	12 Diodes	·."
LWI	Appl. Phys. Lett., Vol.	67. No. 13 (1	995), pp. 1868-1870		•	-	
1	NAKAMURA et al., "C	andela-Class	High-Brightness InGaN/AIGaN Dou	ble-Heterostructu	re Blue-Ligh	t-Emitting	<u></u>
I CWY	Diodes," Appl. Phys. Le	ett. Vol. 64, N	To. 13 (1994), pp. 1687-1689				<u> </u>
	NARUKAWA et al., "R	ecombination	n Dynamics of InGaN Quantum Wells	s by Time-Resolv	ed Photolum	inescence	,"
	Technical Report of the Institute of Electronics, Information and Communication Engineers (Oct. 1996) (Japan),						
	рр. 81-88						
Im			nN Alloy Layer and Its Composition			port of th	ie
IVIV	Institute of Electronics,	Information a	and Communication Engineers (Oct. 1	iolat Samiuand	tor Lucar " N	داتا ندایا	etropies
			ucture of Pulse-Oscillate GaN Blue-V	ioiet Semiconduc	IUI LASEI. IN	INNEL LIE	caomes
	(Jan. 1996) (Japan) No.	elooment of	Blue Device in Final Stage," Electron	ics (Feb. 1006) (1	apan), on. I-	3	
	NAKAMIDA C "I	et Progress is	n Nitride-Based Blue/Green LED and	Semiconductor I	aser," Intern	ational Fo	orum
			so-Bunka Foundation, Inc. (May 1990)				
	Dide Light-Linission	10,000 01 110.	To a distribution, the trial 1990	· / V-F/ FF:			

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U.S. P	PATENT	DOCL	IMENTS
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*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FIUNG DATE
IM5	5,684,309	11/1997	McIntosh et al	257	JA 191	
1	4,862,471	8/1989	Pankove	372	45.01	
	5,646,953	7/1997	Naito et al	372	46.01	
.\	5,642,376	6/1997	Olbright et al	372	4599	
	5,475,700	12/1995	lwata	372	45,01	
	5,247,533	9/1993	Okazaki et al	372	4245.	21
	5,959,307	9/1999	Nakamura et al	257	14	
	5,679,965	10/1997	Schetzina	257	103	
	5,412,226	5/1995	Rejman-Greene et al	257	21	
	5,751,013	5/1998	Kidoguchi et al	257	13	
	5,689,123	11/1997	Major et al	257	190	
	6,005,258	12/1999	Manabe et al	257	13	
IMS	5,247,533	9/1993	Okazaki et al	372	45,01	

FOREIGN PATENT DOCUMENTS

						TRANSLATIO	
	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO
	0 675 552 A1	10/1995	Europe				
	6-21511	1/1994	Japan				
	3-290984	4/1990	Japan				
	4-218994	8/1992	Japan				
	7-074431	3/1995	Japan				Х
	61-156788	7/1986	Japan				X
	08/290218	10/1996	Japan				X
	6-268257	6/1994	Japan				X
	6-177423	6/1994	Japan				X
	7-235723	9/1995	Japan				
	4-68579	3/1992	Japan				
	4-242985	8/1992	Japan				
	6-177423	6/1994	Japan				
	6-21511	1/1994	Japan ·				
	6-237039	8/1994	Japan	٠.			
·	7-297447	11/1995	Japan				
	6-232451	8/1994	Japan			X	
							$\overline{}$

OTHER DOCUMENTS (including Auth r, Titl , Date, Pertinent pages, tc.)

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	Nakamura et al					
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Narukawa et al Phys. Re	ev. B Vol. 55, No. 4, pp R1938-	1941-1/97 Recombination	n dynamics of localized			
	n _{0.05} Ga _{0.95} N multiple quantum wells					
	ys. Lett. 70 (8), pp 981-983, 2/1997 Role of self-formed InGaN quantum dots for					
exciton localization in th	e purple laser diode emitting at	420 nm				
	ys. Lett., Vol. 74, No. 4 pp 558		d nonradiative recombination			
	ight-emitting diode composed of					
Nakamura et al Jpn. J. A Well Structure Laser Did	ppl. Phys., Vol. 35, pp L74-L76	i, Part 2, No. 1B, 1/96 In(GaN-Based Multi-Quantum-			
	ppl. Phys., Vol. 35 (1996), pp.	L217-220, Part 2, No. 2B.	. 2/96 InGaN Multi-			
	Laser Diodes with Cleved Mir.		, _ , _ ,			
	ys. Lett. 69 (11), pp. 1568-1570		arrier lifetime of InGaN			
multi-quantum well struc						
Jpn J. Appl. Phys. Vol. 3	4 (1995) pp. L1332-L1335, Par	t 2, No. 10B, 15 Oct. 199	95, "Superbright Green			
InGaN Single-Quantum-	WII-Structure Light-Emitting D	iodes"	• •			
Technical Report of IEI	CE, ED96-100, CPM96-78 (199	6-10), pp. 15-21				
Technical Report of IEI	E, ED96-110, CPM96-88 (199	6-10), pp. 81-88				

*Examiner Shift Date Considered 12-19-05

Appl. Phys.Lett., 38 (11) June 1981 pp 835-837

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.